

# Abstracts

## Ka-Band GaAs Power FETs

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*Y.-H. Yun, G.C. Taylor, D.S. Bechtle, S.T. Jolly, S.G. Liu and R.L. Camisa. "Ka-Band GaAs Power FETs." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 136-138.*

Ka-band results using submicrometer gate length, air-bridged, soldered flip-chip GaAs power FETs in finline, ridge-waveguide circuits are reported. Conventional photolithography was used to fabricate FETs with submicrometer gate lengths by using the undercut associated with chemical etching. At 35 GHz an output power of 91 mW at 3 dB gain and 4.5% efficiency was measured.

[Return to main document.](#)